

Thesis

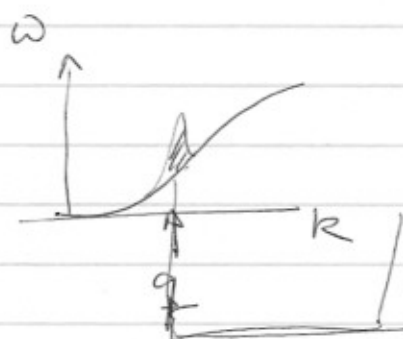
Semiconductors

Electrons in a solid as if they were particles.

⇒ Dispersion $E(k)$

$$\Rightarrow \text{wave} \propto e^{ikx - i\omega(k)t}$$

$$\omega(k) = E(k)/\hbar$$



Wavepacket $\psi(x, t=0)$

$$= A(x) e^{iqx}$$

↑
carrier wave

$A(x)$ includes a mixture of nearby wave-vectors

$$A(x) = \frac{1}{2\pi} \int_{-\infty}^{\infty} dk B(k) e^{ikx}$$

$$\text{Thus } \psi(x, t) = \int dk B(k) e^{i(k+q)x - i\omega(k+q)t}$$

$$\omega(k+q) = \omega(q) + k\omega'(q) + \frac{1}{2}k^2\omega'' + \dots$$

$$\begin{aligned} \psi(x, t) &= e^{i(qx - \omega(q)t)} \\ &\times \int dk B(k) e^{i(kx - \omega'(q)t)} \\ &\times e^{-\frac{1}{2}i\omega''k^2t + \dots} \end{aligned}$$

⇒ Group velocity $v_g = \omega' = \frac{1}{\hbar} \nabla_k E(k)$
Spreading: Diff. const $D = \frac{i\omega''}{2}$

Rate of doing work

$$\frac{d\epsilon}{dt} = \frac{d\epsilon}{dk} \cdot \frac{dk}{dt} = F v_g = \frac{F}{\hbar} \frac{\partial \epsilon}{\partial k}$$

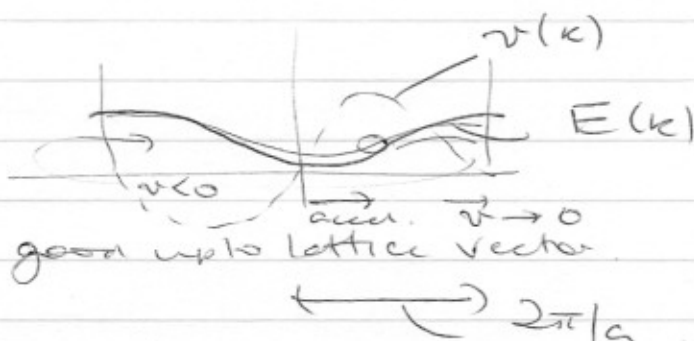
$$\Rightarrow \hbar \dot{k} = F = -e(E + v_g \times B)$$

Electric field: — motion in crystal momentum



Mag field: Conservative — motion along
line of constant energy $\perp$ to B
— orbits along equipotentials.

Block osc



Since $k(t)$ goes up to lattice vector

$\leftarrow \rightarrow 2\pi/a$

— motion in real space oscillates due to repeated bragg refl. — real momentum is transferred to lattice

o Hard to see because of scattering.
(neglected so far)

— k gets very large, easily scattered off disorder, impurities etc

— quantum wells — large spacing, small k — now possible

→ DC in AC out.

Semiconductors — electrons and holes



Filled band in electric field?

- sum over all states $\rightarrow 0$
- one removed?

Holes: ① $k_h = -k_e$ (optical obs.)

② $\mathcal{E}_h(k_h) = -\mathcal{E}_e(k_e)$ (adding hole requires work)

③ $v_h \propto \nabla_{k_h} \mathcal{E}(k_h) \propto \nabla_{k_e} \mathcal{E}(k_e) = v_e$ (vel)

④ Effective mass: quadratic dispersion

$$\mathcal{E} = \mathcal{E}_0 + \frac{\hbar^2 k^2}{2m^*} \quad m_h^* = -m_e^*$$

⑤ Charge +ve

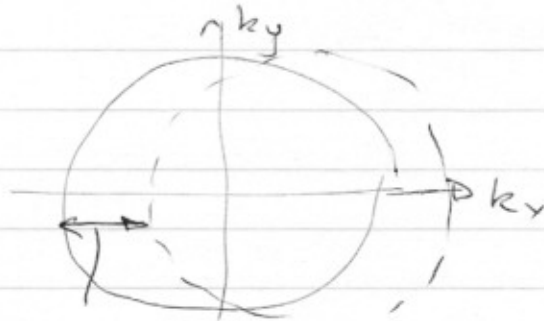
$$\hbar \dot{k}_e = -e(E + v_e \times B)$$

$$\hbar \dot{k}_h = +e(E + v_h \times B)$$

Scattering — frictional force

$$\hbar \dot{k} = F - \frac{\hbar k}{\tau}$$

— relaxation of distribution to eqn^m in characteristic time τ .



Shift
by $\delta k = -e E \tau$
 $\hbar$

$$\Rightarrow \delta v = \delta k / m^* \quad (\text{parabolic band})$$

$$j = -ne \delta v = \underbrace{ne^2 \tau}_{\frac{1}{m^*}} E$$

$$\sigma = ne \mu \quad \mu = e \tau / m^* \quad \text{mobility.}$$

Coursed

Transport in E & B fields

$$\hbar \vec{k} + \hbar \frac{\vec{k}}{\tau} = e(\vec{E} + \vec{v} \times \vec{B})$$

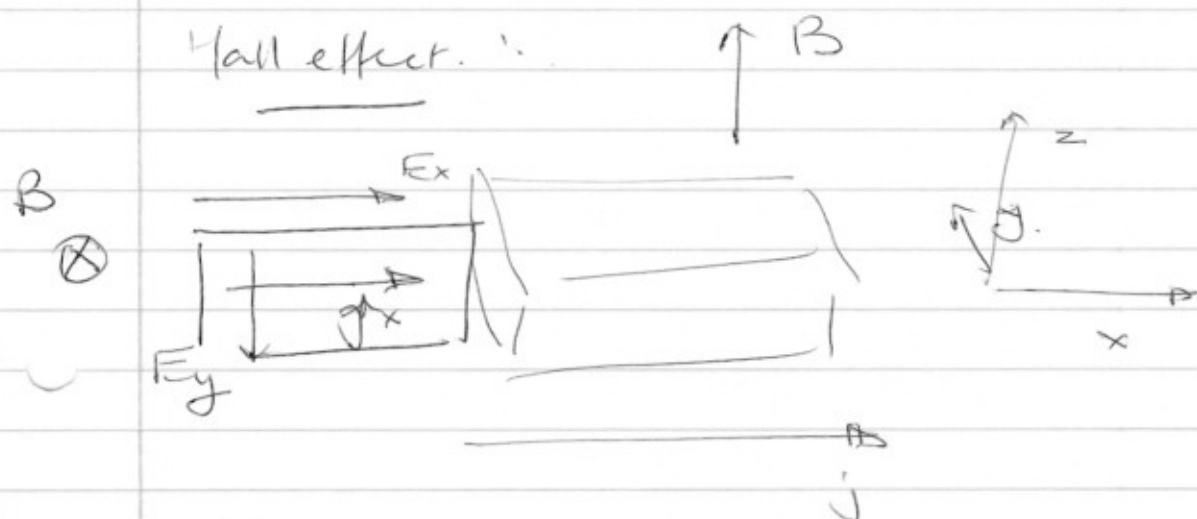
Stationary state $B \sim \hat{z}$
 E in x - y plane
 Parabolic bands $\hbar \vec{k} = m \vec{v}$

$$v_z = -\frac{e\tau}{m} E_z \quad (1)$$

$$v_x = -\frac{e\tau}{m} E_x - \beta v_y \quad (2)$$

$$v_y = -\frac{e\tau}{m} E_y + \beta v_x \quad (3)$$

$$\beta = \frac{eB\tau}{m} = \omega_c \tau = \mu B$$

Hall effect:

If current flows in x dirⁿ only

$$\Rightarrow v_y = 0 \quad \therefore v_x = -\frac{e\tau}{m} E_x \quad \text{from (2)}$$

$$\beta v_x = \frac{e\tau}{m} E_y \quad \text{from (3)}$$

$$\text{or } E_y = -\beta E_x$$

At large fields $\beta \gg 1$ so electric field normal to current flow

Useful measure.

Hall
coeff. $R_H = \frac{E_y}{j \times B} = -\frac{1}{ne}$

- depends on density
- on sign of carriers (+ve for holes)